

b) Amendments to the Specification

Please substitute the paragraph at page 1, after the Title with the following replacement paragraph:

This application is a Division of Application No. [:] 09/074,699, filed May 8, [[1999]] 1998, now U.S. Patent No. 6,346,184 B1.

Kindly substitute the following replacement paragraph for paragraph [0088] on page 16.

--[0088] Band Band gap of the first i layer 402 < band gap of the second i layer 405 < band gap of the third i layer 408. As each of the doped layers, a n-type semiconductor layer (n layer) or a p-type semiconductor layer (p layer) can be used.--